MA3075WALT1G, SZMA3075WALT1G

Zener ESD Protection Diode

SOT-23 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Fasturas

- SOT–23 Package Allows Two Separate Unidirectional Configurations
- Low Leakage $< 1 \mu A @ 5.0 V$
- Breakdown Voltage: 7.2-7.9 V @ 5 mA
- Low Capacitance (80 pF typical @ 0 V, 1 MHz)
- ESD Protection Meeting: 16 kV Human Body Model

30 kV Air and Contact Discharge

- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Void Free, Transfer-Molded, Thermosetting Plastic Case
- Corrosion Resistant Finish, Easily Solderable
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|----------------|-------------|
| Peak Power Dissipation @ 100 μs (Note 1) | P _{pk} | 15 | W |
| Steady State Power Dissipation Derate above 25°C (Note 2) | P _D | 225 1.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 556 | °C/W |
| Maximum Junction Temperature | $R_{\theta JA}$ | 417 | °C/W |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | – 55 to +150 | °C |
| ESD Discharge MIL STD 883C – Method 3015–6 IEC61000–4–2, Air Discharge IEC61000–4–2, Contact Discharge | V _{PP} | 16 30 30 | kV |

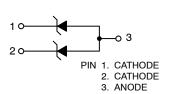
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Non-repetitive 100 μs pulse width
- 2. Mounted on FR-5 Board = 1.0 X 0.75 X 0.062 in.



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SOT-23 CASE 318 STYLE 12

MARKING DIAGRAM



7W5 = Specific Device Code

M = Date Code*
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|---------------------|-----------------------|
| MA3075WALT1G | SOT-23 (Pb-Free) | 3000 / Tape & Reel |
| SZMA3075WALT1G | SOT-23 (Pb-Free) | 3000 / Tape & Reel |

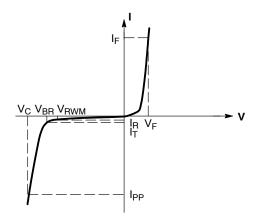
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MA3075WALT1G, SZMA3075WALT1G

ELECTRICAL CHARACTERISTICS

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|-----------------|------------------------|-----|-----|-----|-------|
| Forward Voltage | V _F | I _F = 10 mA | | 0.8 | 0.9 | V |
| Zener Voltage*2 | V _Z | I _Z = 5 mA | 7.2 | 7.5 | 7.9 | V |
| Operating Resistance | R _{ZK} | $I_Z = 0.5 \text{ mA}$ | | | 120 | Ω |
| | R_Z | I _Z = 5 mA | | 6 | 15 | Ω |
| Reverse Current | I _{R1} | V _R = 5 V | | | 1 | μΑ |
| | I _{R2} | V _R = 6.5 V | | | 60 | μΑ |
| Temperature Coefficient of Zener Voltage*3 | S _Z | I _Z = 5 mA | 2.5 | 4.0 | 5.3 | mV/°C |
| Terminal Capacitance | Ct | V _R = 0 V | | 80 | | pF |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Uni-Directional

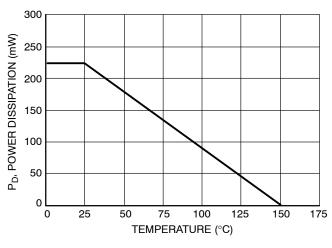


Figure 1. Steady State Power Derating Curve

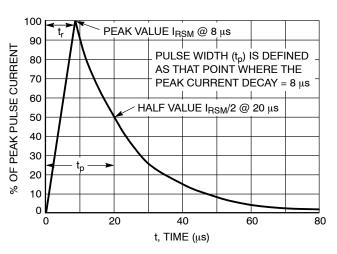


Figure 2. 8 X 20 µs Pulse Waveform

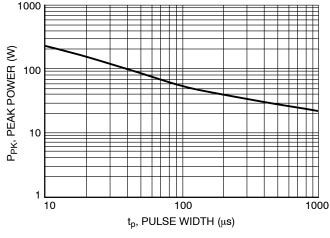


Figure 3. Pulse Rating Curve

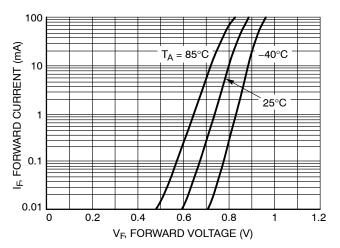


Figure 4. Forward Current versus Forward Voltage

MA3075WALT1G, SZMA3075WALT1G

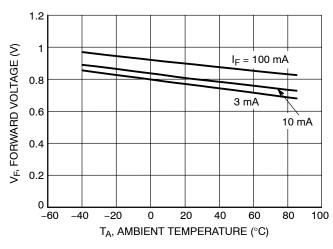


Figure 5. Forward Voltage versus Temperature

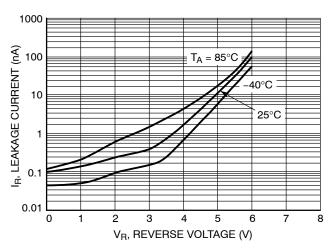


Figure 6. Leakage Current versus Reverse Voltage

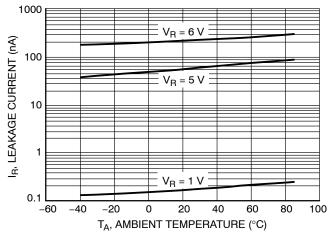


Figure 7. Leakage Current versus Temperature

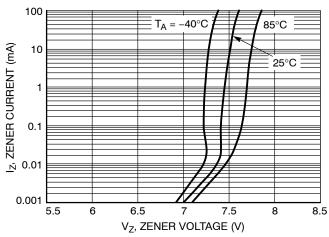


Figure 8. Zener Current versus Zener Voltage

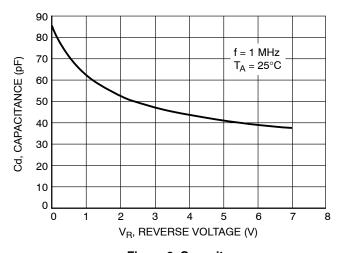


Figure 9. Capacitance

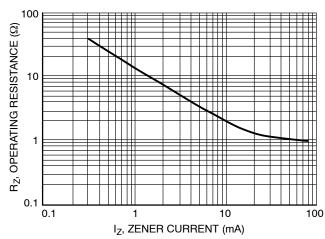


Figure 10. Operating Resistance versus Zener Current

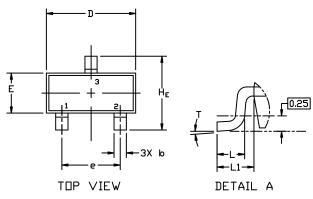


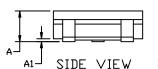


SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | INCHES | | | |
|-----|-------------|------|--------|-------|-------|-------|
| DIM | MIN. | N□M. | MAX. | MIN. | N□M. | MAX. |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| С | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| Ε | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | 0* | | 10° | 0* | | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | 1 | |
|---|---|---|---|---|---|
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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